

Ryszard Piotrkowski

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

230
citations

1163117

8
h-index

1372567

10
g-index

10
all docs

10
docs citations

10
times ranked

187
citing authors

#	ARTICLE	IF	CITATIONS
1	Band Structure of HgTe. Physica Status Solidi (B): Basic Research, 1965, 8, K135.	1.5	64
2	Temperature dependence of electrical properties of gallium-nitride bulk single crystals doped with Mg and their evolution with annealing. Journal of Applied Physics, 2001, 89, 7960-7965.	2.5	44
3	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	3.3	31
4	Self-compensation of carbon in HVPE-GaN:C. Applied Physics Letters, 2020, 117, .	3.3	21
5	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. Journal of Applied Physics, 2010, 108, 023516.	2.5	17
6	Towards proper characterization of nonlinear metal-semiconductor contacts. Generalization of the transmission line method. Applied Physics Letters, 2011, 99, .	3.3	17
7	Pressure-induced Slow Relaxation of the Free Electron Concentration in Undoped n-type InSb. Physica Status Solidi (B): Basic Research, 1976, 73, K131.	1.5	16
8	Kinetics of low-temperature activation of acceptors in magnesium-doped gallium nitride epilayers grown by metal-organic vapor-phase epitaxy. Journal of Applied Physics, 2006, 99, 033703.	2.5	8
9	The Dependence of Thermoelectric Power and Conductivity of n-type Indium Antimonide on Hydrostatic Pressure. Physica Status Solidi (B): Basic Research, 1969, 31, K103.	1.5	7
10	High temperature electrical transport properties of MBE-grown Mg-doped GaN and AlGaIn materials. Journal of Applied Physics, 2020, 128, .	2.5	5